On-chip memories at the edge

Kevin J. M. Martin

On-chip memories at the edge

The edge of memories

Kevin J. M. Martin
Maître de conférences

Univ. Bretagne-Sud
UMR CNRS 6285, Lab-STICC
Lorient, France

14/06/2022, AMLE summer school, Lorient

It's the Memory, Stupid!

Richard Sites, lead designer of the DEC Alpha, 1996

*I expect that over the coming decade memory subsystems design will be the **only** important design issue for microprocessors.*

Most of his colleagues designing next-generation Alpha architectures at Digital Equipment Corp. ignored his advice and instead remained focused on building ever faster microprocessors, rather than shifting their focus to the building of ever faster *systems* [8].

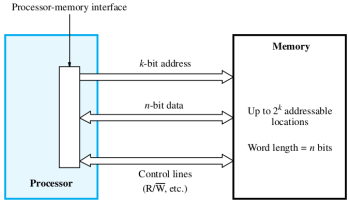
N.B.: Digital Equipment Corp. no longer exists

What memory is needed for?

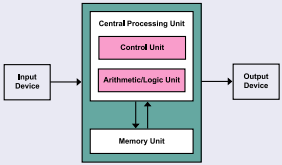
- storing data
- storing instructions
- saving temporary values
- synchronizing processes/threads

Connection of the memory to the processor

Von Neumann vs Harvard Architecture

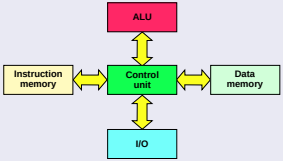


Von Neumann Architecture



- 1945
- common bus for instruction and data

Harvard Architecture



- 1944
- separate bus for instruction and data

The ideal memory is

- fast
- large
- inexpensive

Impossible to meet these three requirements

- physical properties of memories: area, delay, energy consumption
- economical issues
- $\nearrow$ speed + $\nearrow$ size = $\nearrow$ cost
- $\nearrow$ size $\Rightarrow$ $\searrow$ speed

Different solutions and structures exist

- different technologies
- different organisations
- for different needs (permanent store, operating store, fast store)

Memory hierarchy

The processor designer would choose

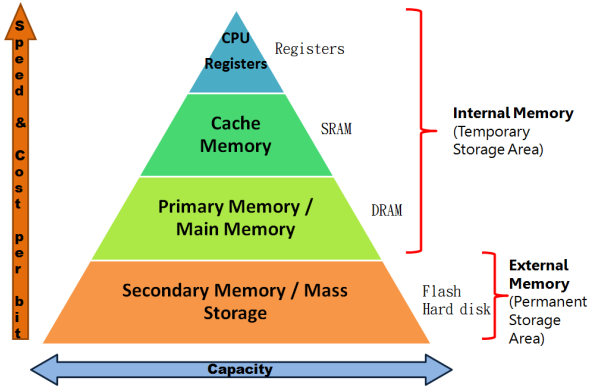
speed

The user would choose

size

The manufacturer would choose

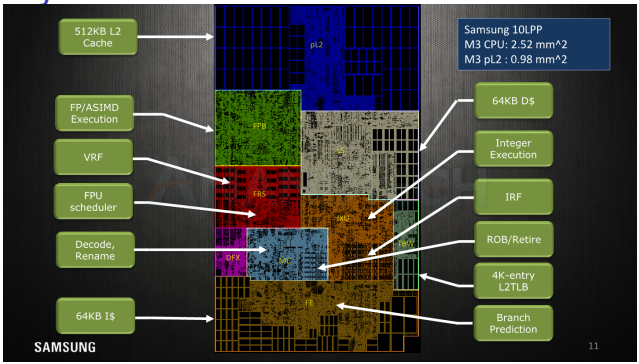
cost



Source: not me

Memory hierarchy as an enabler

Exynos M3 Core Layout



Source: www.anandtech.com

- pL2: Private L2 cache, 512KB
- FPB: Floating point data path
- FRS: Floating point schedulers
- MC: Mid-core, the decoders and rename units.
- DFX: This is for debug/test logic
- LS: Load/store unit along with the 64KB of L1 data cache
- IXU: Integer execution unit; execution units, schedulers, integer physical register file memories.
- TBW: Transparent buffer writes, includes the TLB structures.
- FE: The front-end including branch predictors, fetch units and the 64KB L1 instruction cache memories.

Insight on current challenges

- more than 80% of the chip area is dedicated to caches, memories, memory controllers, interconnects and so on, whose sole purpose is to buffer data or control the buffering of data [1]

$\Rightarrow$ workarounds which are making systems ever more complex

- more than 62% of the entire measured system energy is spent on moving data between memory and the computation units [1]

Content

This lecture will cover

- Basic memory organisations
- Overview on memory technologies
- Memory system
  - Caches
  - Virtual memory
- The future
  - Emerging memory technologies
  - Near-memory computing, Computing in Memory

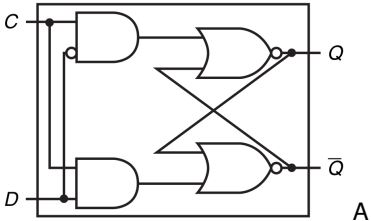
This lecture will NOT cover

- Massive storage (Hard Disk drives, magnetic or optical drives, etc.)
- Exhaustive DRAM features (timing, controller, protocol, system)
- I/O Topics
- Detailed cache coherence

Flip-Flops and Latches

Definition

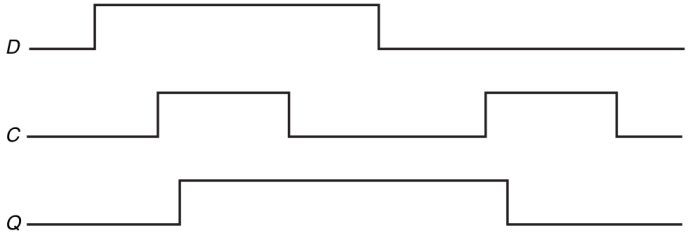
- latch: A memory element in which the output is equal to the value of the stored state inside the element and the state is changed whenever the appropriate inputs change and the **clock is asserted**
- D latch: A latch with **one data input** (called *D*) that stores the value of that input signal in the internal memory



A

D latch implemented with NOR gates

Source: [11]

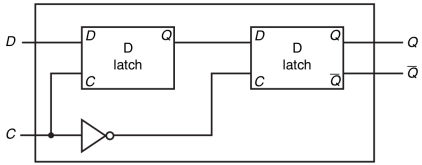


Operation of a D latch, assuming the output is initially deasserted

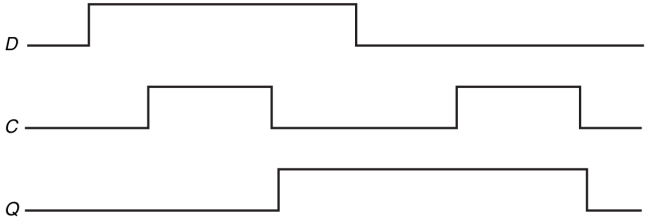
D flip-flop

Definition

- flip-flop: A memory element for which the output is equal to the value of the stored state inside the element and for which the internal state is changed **only on a clock edge**
- D flip-flop: A flip-flop with **one data input** (called *D*) that stores the value of that input signal in the internal memory when the **clock edge occurs**



A D flip-flop with a falling-edge trigger



Operation of a D flip-flop with a falling-edge trigger, assuming the output is initially deasserted

Source: [11]

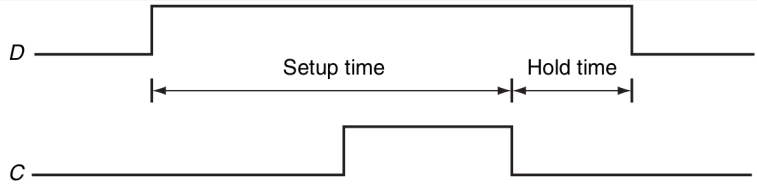
D flip-flop

Timing

The D input is sampled on the clock edge, it must be valid for a period of time immediately before and immediately after the clock edge

Definition

- Setup time: the minimum time that the input to a memory device must be valid before the clock edge
- Hold time: the minimum time during which the input must be valid after the clock edge



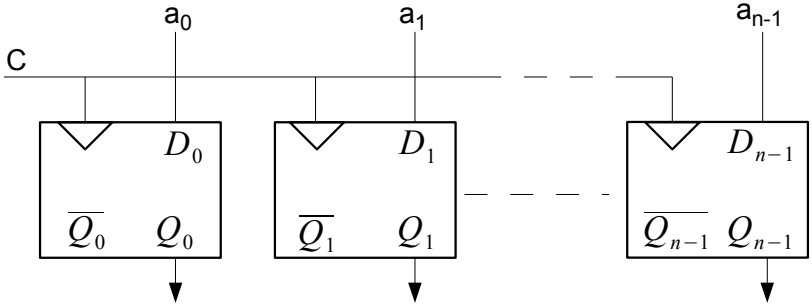
Setup and hold time requirements for a D flip-flop with a falling-edge trigger

Source: [11]

Registers

Definition

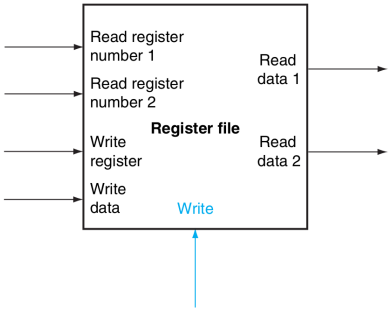
- Register: an array of D flip-flops that can hold a multibit datum, such as a byte or word



Registers and register files

Register File

- Set of registers
- Specify the register number to be accessed
- One decoder per read or write port
- **Central structure of the datapath of a processor**



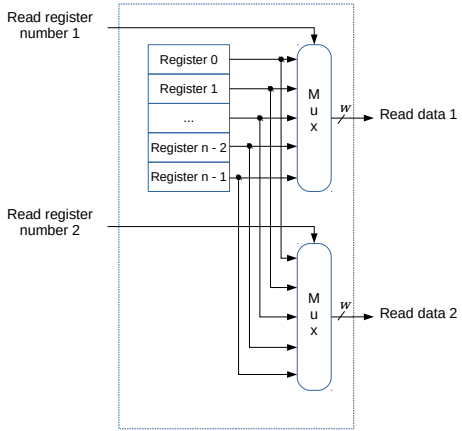
A register file with two read ports and one write port has five inputs and two outputs

Registers and register files

Reading a value

Read operation

- Input: register number
- Output: data contained in that register



Implementation of two read ports for a register file with n registers with a pair of n-to-1 multiplexors, each *w* bits wide

Registers and register files

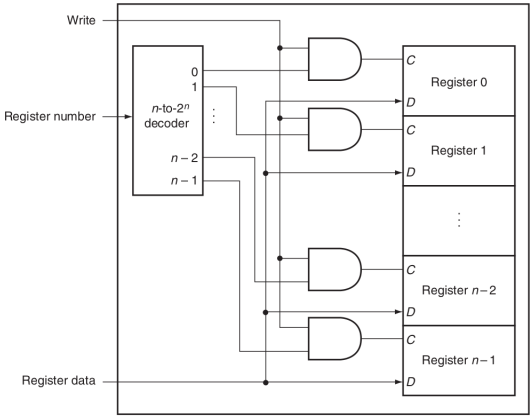
Writing a value

Write operation

- 3 inputs:
  1. register number
  2. data value
  3. clock (write signal)

Timing constraints

Setup and hold-time constraints to ensure that the correct data is written into the register file



The write port for a register file is implemented with a decoder that is used with the write signal to generate the *C* input to the registers

Registers and register files

Register file parameters

- Size (number of registers)
- Number of ports
- Width? (usually set by data width)

Size

- Too small: register *spilling*
- Too large: static energy, extra chip area

The tricky thing

Reading the value currently being written (in the same clock cycle)

Number of ports

- nonlinear cost function of the number of ports
  - (partitioned register files for some VLIW processors)
- 2 read ports + 1 write port: good trade-off

Registers and register files

Unsuited for big memories

Bigger memories

Small memories are built using registers and register files:

- configuration registers
- pipeline registers
- processor register file (32x32 = 128 B)

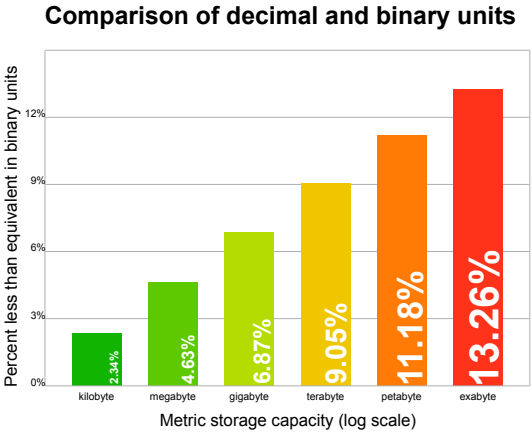
Bigger memories are built upon another organisation

Measuring memory size

Power of 2 vs power of 10

Unit multiples of the octet (byte) may be formed with SI prefixes and binary prefixes (power of 2 prefixes) as standardized in 1998 [2]

- 1 Byte = 8 bits
- 1 kilobyte (kB) = 10^3 bytes
  = 1 000 bytes
- 1 kibibyte (KiB)= 2^{10} bytes
  = 1 024 bytes
- ...



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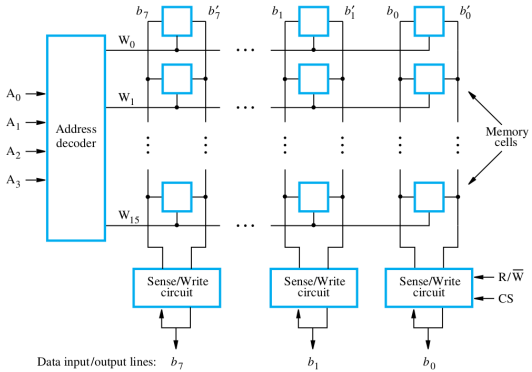
Internal Organisation of Memory Chips

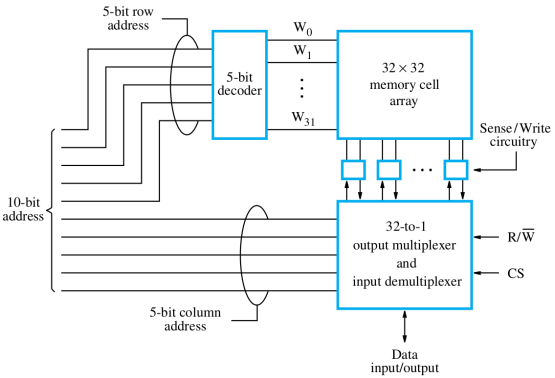


Memory cells organized in the form of an array

Definition

- height: the number of addressable locations
- width: the number of bits per unit

Internal Organisation of Memory Chips



Organization of a 1K x 1 memory chip

Impact on the number of wires

Example with storing 1024 bits

	1K x 1	128 x 8	32 x 32
CS	1	1	1
$R/\overline{W}$	1	1	1
VCC	1	1	1
GND	1	1	1
Data	1	8	32
Address	10	7	5
Σ	15	19	41

Narrow configurations

Fastest and newest memories use narrow configurations (x1 or x4)

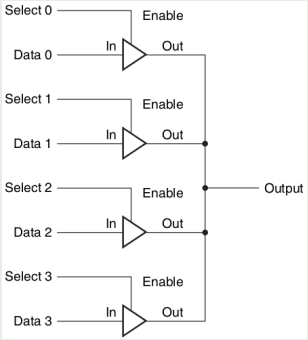
Internal Organisation of Memory Chips

The output multiplexor

Large memory

A 64K-to-1 multiplexor that would be needed for a 64K x 1 memory is totally impractical!

Tri-State Buffers



Four three-state buffers are used to form a multiplexor

Two inputs:

- data signal
- Output enable

One output with three states:

- asserted
- deasserted
- high impedance

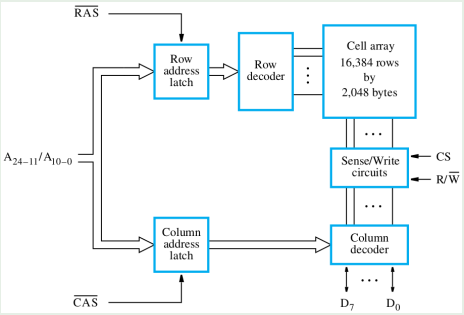
Internal Organisation of Memory Chips

The decoder

Large memory

A 4M x 8 memory, we would need a 22-to-4M decoder and 4M word lines!

Rectangular arrays and two-step decoding process



Internal organization of a 32M x 8 memory chip

- 16K x 16K array
- 16,384 cells in each row divided into 2,048 groups of 8 $\Rightarrow$ 2,048 bytes of data
- 14 address bits to select a row, 11 address bits needed to select a column
- Multiplexing the wires
  - RAS: Row Access Strobe
  - CAS: Column Access Strobe

Internal Organisation of Memory Chips

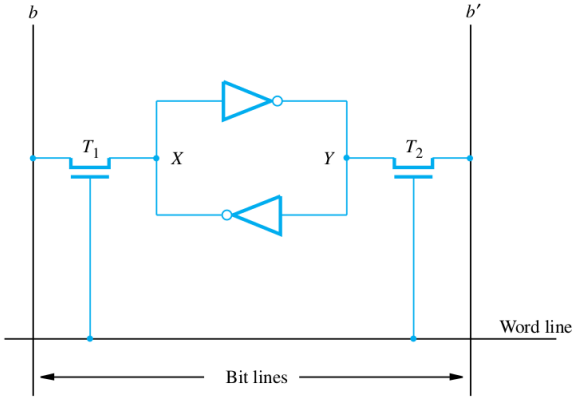
The memory cell can be:

- SRAMs (static random access memories)
- DRAMs (dynamic random access memories)

SRAM

Definition

Static Memory: *Memory capable of retaining its state as long as power is applied* [5]



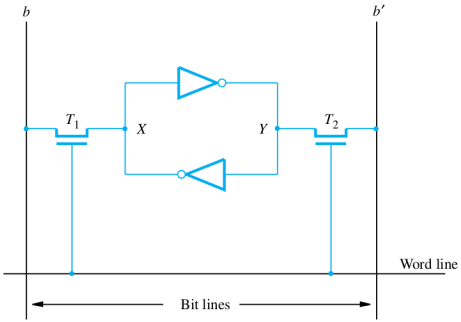
Source: [5]

SRAM: Static Random Access Memory

- Two inverters cross-connected to form a latch
- Two bit lines (T1 and T2)
- *b* and *b'* are always complements

SRAM

Reading and writing an SRAM cell



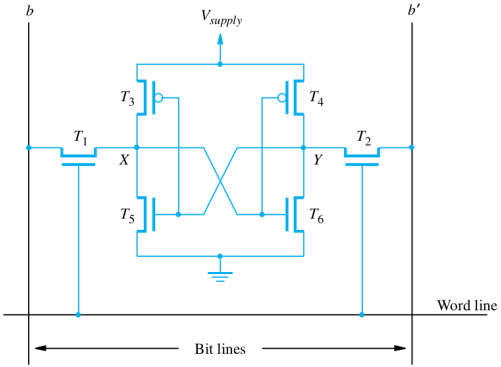
Read Operation

1. The word line is activated to close switches T_1 and T_2
2. The Sense/Write circuit at the end of the two bit lines monitors their state

Write Operation

1. The word line is activated to close switches T_1 and T_2
2. The Sense/Write circuit drives bit lines b and b', instead of sensing their state

Overview of memory technologies



CMOS implementation of 6T SRAM memory cell [5]

CMOS SRAM cell

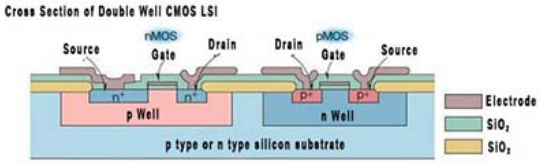
- Transistor pairs (T_3 , T_5) and (T_4, T_6) form the inverters in the latch
- Continuous power is needed for the cell to retain its state
- Content lost when power down
- Back in stable state when power on (but maybe not the same state)

Volatile memory

SRAMs are *volatile memory* because their loose their content when power is shut down

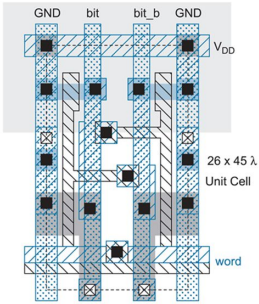
Overview of memory technologies

SRAM CMOS physical design

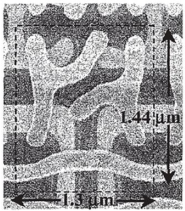


Source: http://www.shmj.or.jp/innovation50/english/detail_D05E.htm

Layout of 6T SRAM Cell



Only poly and diff layers are shown.



Source:Digital Design: Principles and Practices, Published by Jonas Wilkerson

SRAM

Pros and cons

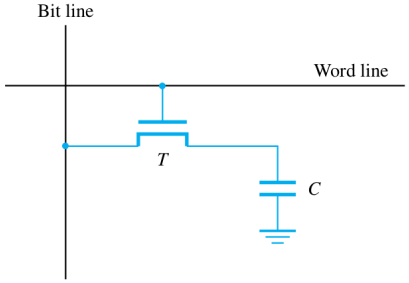
SRAM strong points

- Same fabrication process as logic circuit
  - Good integration on processor die
  - Ideal candidate for cache implementation
- Low power consumption
- Fast (+fixed access time)

SRAM weak points

- Expensive
- Low density

DRAM



Source: [5]

DRAM: *Dynamic* Random Access Memory

- A capacitor C
- A transistor T

Why is it called *Dynamic*?

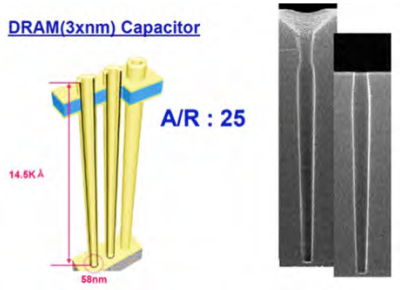
The capacitor can retain its state for tens of milliseconds only.
Need to *refresh* periodically.

Volatile memory

DRAMs are *volatile memory* because their loose their content when power is shut down

Overview of memory technologies

DRAM physical design



Source: [7]

Did you know?

DRAM's capacity has been one of the more consistent incarnations of Moore's law [7]

- scaled in capacity by a factor of over 16 million
- 1 kbits on a die in 1970 to 16 Gbits in 2020

SDRAM: *Synchronous* DRAM

Synchronisation with a clock signal

- built-in refresh circuitry (hides the dynamic feature of DRAM to the user)
- *burst* mode: starting address + burst length

Definition

Page: a large block of data

Fast Page Mode

Transfer a *page* of data: all bytes of the selected row in sequential order

- no need to reselect the row
- successive CAS signals

DRAM

DDR: Double-Data-Rate SDRAM

- Transfer data on both rising and falling edge of the clock
- Open standard

Rambus Memory

- Differential-signaling technique to transfer data to and from the memory chips
- Proprietary scheme that must be licensed

DRAM

Pros and cons

DRAM strong points

- High density
- Low cost per bit

DRAM weak points

- Must be refreshed periodically
- Hard integration of DRAM with logic technology
- Slower than SRAM

DRAM

Memory controller

In charge of:

- 2 steps access: row + column, RAS + CAS signals
- chip select: when multiple memory modules
- refresh: periodic read cycles of asynchronous DRAM

Refresh overhead

- When internal refresh operation occurs, the memory cannot respond
- Typically few percent of the total time available for accessing the memory
- Still ongoing research activities
  - Goal: hide completely the refresh

Memory technology comparison

Technology	Bytes per Access (typ.)	Latency per Access	Cost per Megabyte[a]	Energy per Access
On-chip Cache	10	100 of picoseconds	$1–100	1 nJ
Off-chip Cache	100	Nanoseconds	$1–10	10–100 nJ
DRAM	1000 (internally fetched)	10–100 nanoseconds	$0.1	1–100 nJ (per device)
Disk	1000	Milliseconds	$0.001	100–1000 mJ

Source: [8]

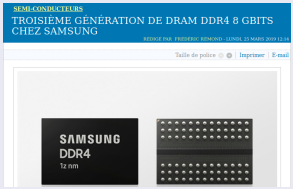
Choice of technology

- SRAM: small but very fast memory
- DRAM (DDR SDRAM): main memory

Memory chips

Static memory chip

Dynamic memory chip



Overview of memory technologies

Emerging technologies

Patience, grasshoper. . .

This is discussed later

ROM

Read Only Memory

Volatile memory

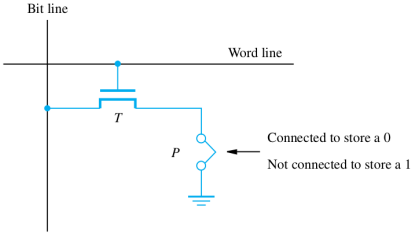
SRAMs and DRAMs are *volatile memory*

Non Volatile memory

Need to store software and data and not loose information when power is shut down

ROM

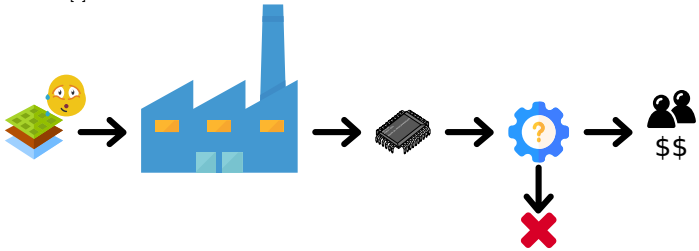
Read Only Memory



Configure point P

- Ground: value 0 stored
- Not connected: value 1 stored

Source: [5]

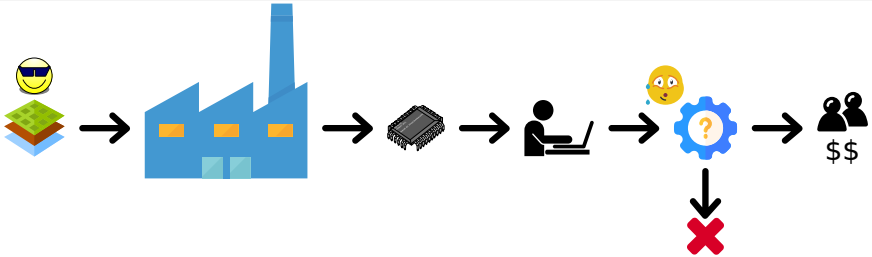


PROM

Programmable Read Only Memory

PROM

“Programmable” through a fuse



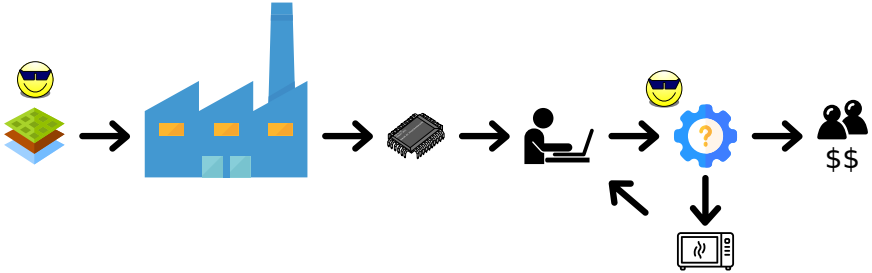
EPROM

Erasable Programmable Read Only Memory

EPROM

"Erasable and Programmable" through a *special transistor*

Expose the chip to ultraviolet light to erase

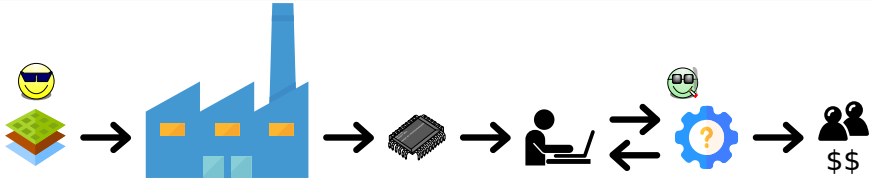


EEPROM

Electrically Erasable Programmable Read Only Memory

EEPROM

different voltages are needed for erasing, writing, and reading the stored data ⇒ circuit complexity



Flash Memory

Flash Memory

- read the contents of a single cell
- write an entire block of cells

Flash Cards

Flash drives (SSD)

2 To, SATA 3 (6 Gb/s), 2,5"

Types of memories

The sore point

volatile vs non-volatile

RAM vs ROM

RAM: Random Access Memory

RAM = volatile?

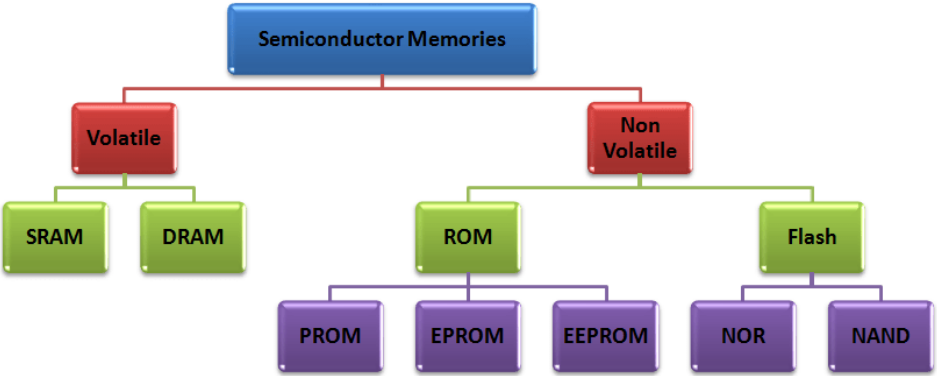
ROM: Read Only Memory

ROM = non-volatile?

What about writing data in a non-volatile memory?

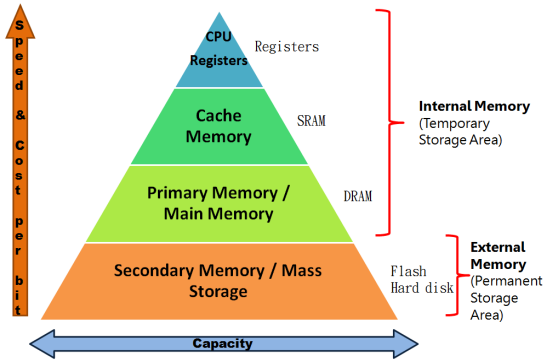
e.g. Hard disk drive, USB key, ...

Memory classification



Source: [12]

Overview of computer memory organisation



From the I/O device to the processor

The data need to move across the levels

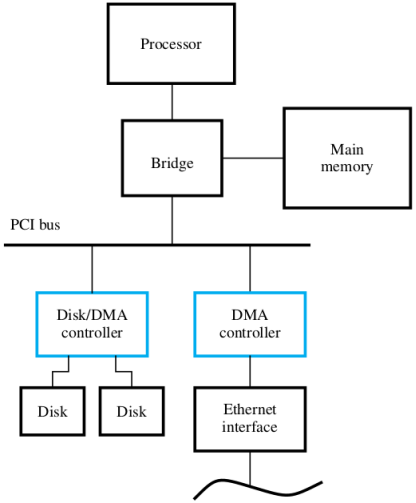
- From the I/O to the main memory
- From the main memory to the cache
- From the cache to CPU registers

Managing data movement

Offload the processor from weighty data movement tasks

The memory system

Direct Memory Access



DMA

A special control unit to manage the transfer, without continuous intervention by the processor

Under supervision (usually operating system)

- Processor provides:
  - starting address
  - the number of words in the block
  - the direction of the transfer
- DMA raises an interrupt when finished

Caches

The illusion of a large memory

accessible as fast as a small memory [11]

Idea

A processor does not need to access all of the program codes and data at once. Let's keep near the useful parts.

Principle of locality

- Temporal locality (locality in time): if an item is referenced, it will tend to be referenced again soon.
- Spatial locality (locality in space): if an item is referenced, items whose addresses are close by will tend to be referenced soon.

Caches

Definition

- *block* or *line*: the minimum unit of information that can be either present or not present in a cache.
- *hit*: the data requested is present in the cache
- *miss*: the data requested is NOT present in the cache
- *hit rate* or *hit ratio*: the fraction of memory accesses found in the upper level
- *miss rate* (1 - hit rate): the fraction of memory accesses NOT found in the upper level

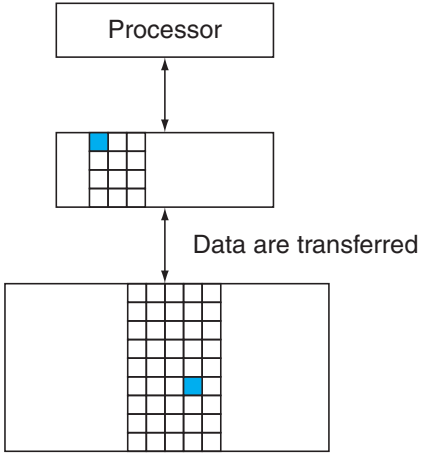
Caches

Message to programmers

No, memory is NOT a flat, random access device

You need to understand memory hierarchy to get good performance

The big picture



Source: [11]

Memory hierarchy

- upper and lower level
- transfer entire block between levels

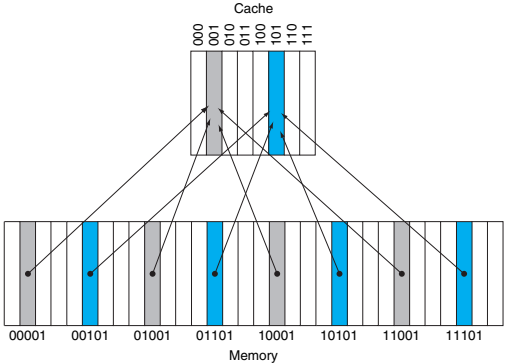
Caches

Direct-map cache

Direct-mapped cache

A cache structure in which each memory location is mapped to exactly one location in the cache

Position = (Block number) modulo (Number of *blocks* in the cache)



Source: [11] A direct-mapped cache with eight entries showing the addresses of memory words between 0 and 31 that map to the same cache locations

Simple to implement

High miss rate

Fully Associative Cache

A cache structure in which a block can be placed in any location in the cache

Low miss rate

Hardware cost

Caches

n-way set-associative cache

set-associative cache

- A cache that has a fixed number of locations (at least two) where each block can be placed
- Each block in the memory maps to a unique set in the cache
- A block can be placed in *any* element of that set
- n is the number of places in the set

Good trade-off between direct-map and fully associative

Finding the good trade-off!

Which block to replace?

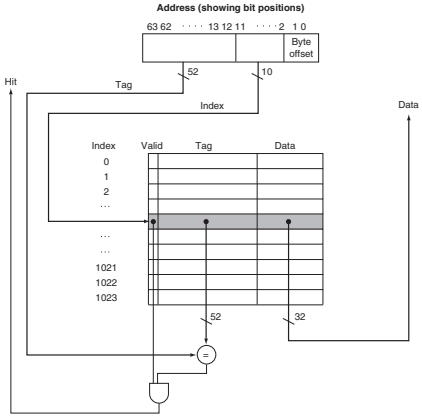
- Intuitively, replace the one that has gone the longest time without being referenced
  - *Least Recently Used* (LRU)
  - keep track of all references by means of counters
- The simplest algorithm: randomly choose the block to be replaced
  - quite effective in practice
- Many others:
  - FIFO (*First In First Out*)
  - LFU (*Least Frequently Used*)
  - pseudo-LRU

Caches

Tags

Definition

- *Tag*: A field in a table used for a memory hierarchy that contains the address information required to identify whether the associated block in the hierarchy corresponds to a requested word
- *Valid bit*: A field in the tables of a memory hierarchy that indicates that the associated block in the hierarchy contains valid data



The lower portion of the address is used to select a cache entry consisting of a data word and a tag [11]

Caches

Tags

Size of tags versus associativity

Increasing associativity requires more comparators and more tag bits

Cache of 4096 blocks, four-word block size, 64-bit address

16 bytes per block $\Rightarrow$ 64-4=60 bits for index and tag

- Direct-map cache
  - number of sets = number of blocks $\Rightarrow$ 12 bits of index ($log_2(4096) = 12$)
  - $(60 - 12) \times 4096 = 192$ Ki tag bits
- Two way associative cache
  - number of sets = 2048 $\Rightarrow$ 11 bits of index ($log_2(2048) = 11$)
  - $(60 - 11) \times 2 \times 2048 = 196$ Ki tag bits
- Fully associative cache
  - number of sets = 1 $\Rightarrow$ 0 bits of index ($log_2(1) = 0$)
  - $60 \times 1 \times 4096 = 240$ Ki tag bits

Size of tags versus associativity

Increasing associativity requires more comparators and more tag bits

Size given by the manufacturer

The size of the cache given by the manufacturer does not include the size of tags + valid bit.

Content Addressable Memory

A circuit that combines comparison and storage in a single device

- RAM: supply address, return data
- CAM: supply data, return index

Caches

Handling writes

Consistency

When the cache and the main memory have different values, they are *inconsistent*

Write-through

- Always update cache AND next lower level of the hierarchy
- Processor is *stall* during writing to main memory ($\approx$ 100 cycles)
- Use of *write buffer* to free the processor

Write-back

- Update the cache only
- Update next lower level when the block is replaced
- Improve performance but more complex to implement

Caches

Split cache

Two independent caches

- instruction cache
- data cache

operating in parallel

Harvard computer style

Can the split cache be considered as an implementation of Harvard architecture?

Caches

Multilevel cache

Close the gap between primary cache and DRAM

- Primary cache: focus on minimizing hit time
  - Smaller block size, reduce miss penalty
- Secondary cache: focus on minimizing the miss rate
  - Larger total size, higher associativity

Caches

Cannot reach 0% miss

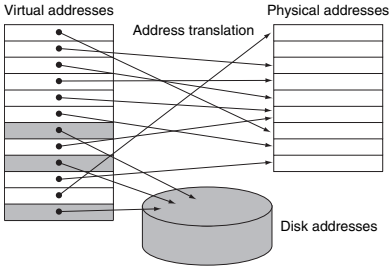
The three Cs: behavior of memory hierarchies

- *Compulsory miss* (or *cold-start miss*): A cache miss caused by the first access to a block that has never been in the cache
- *Capacity miss*: A cache miss that occurs because the cache, even with full associativity, cannot contain all the blocks needed to satisfy the request
- *Conflict miss*: A cache miss that occurs in a set-associative or direct mapped cache when multiple blocks compete for the same set and that are eliminated in a fully associative cache of the same size

Virtual memory

Two historical motivations

1. efficient and safe sharing of memory among several programs
2. remove the programming burden of a small limited amount of main memory



In virtual memory, blocks of memory (called pages) are mapped from one set of addresses (called virtual addresses) to another set (called physical addresses) [11]

Size of virtual address space

- A 32-bit processor can address up to $2^{32} = 4Gi$ elements
- A 64-bit processor can address up to $2^{64} = 16Ei$ (exbi) elements ($> 10^{18}$)

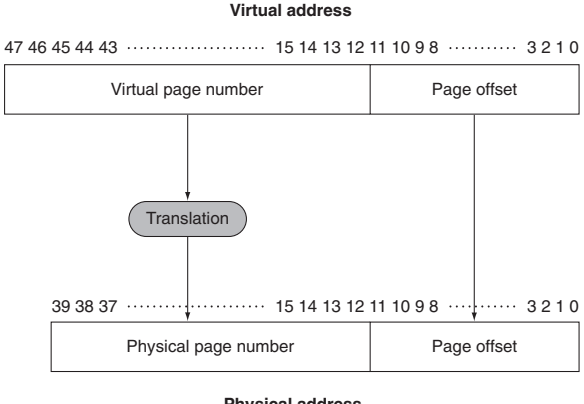
Virtual memory

Definition

- Virtual memory: A technique that uses main memory as a “cache” for secondary storage
- Physical address: An address in main memory
- Protection: A set of mechanisms for ensuring that multiple processes sharing the processor, memory, or I/O devices cannot interfere, intentionally or unintentionally, with one another by reading or writing each other’s data. These mechanisms also isolate the operating system from a user process
- Page fault: An event that occurs when an accessed page is not present in main memory
- Virtual address: An address that corresponds to a location in virtual space and is translated by address mapping to a physical address when memory is accessed
- Address translation (or address mapping): The process by which a virtual address is mapped to an address used to access memory

Virtual memory

Mapping



Mapping from a virtual to a physical address. The page size is $2^{12} = 4$ KiB. The number of physical pages allowed in memory is 2^{28}, since the physical page number has 28 bits in it. Thus, main memory can have at most 1 TiB, while the virtual address space is 256 TiB [11]

Virtual memory

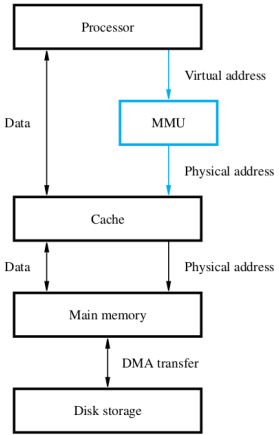
High cost of a page fault

Enormous miss penalty: 1 page fault = millions of clock cycles

Key decisions:

- Page should be large enough to amortize the high access time (4 KiB to 64 KiB)
- Allow fully associative placement
- Software page handling (faults and placement)
- Write-back (write-through takes too long)

Virtual memory



Virtual memory organization [5]

Memory Management Unit (MMU)

- keeps track of which parts of the virtual address space are in the physical memory
- translates the virtual address into the corresponding physical address

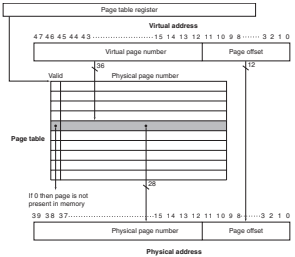
Virtual memory

Placing a page and finding it again

Definition

Page Table: the table containing the virtual to physical address translations

- stored in memory, indexed by the virtual page number
- each entry in the table contains the physical page number for that virtual page



- Each program has its own page table
- *page table register*: the start of the page table
- *valid bit*: page present or not in memory

The page table is indexed with the virtual page number to obtain the corresponding portion of the physical address [11]

Virtual memory

Page faults

- Page fault when the valid bit for a virtual page is off
- Software exception
- Operating system gets control
  - find the page
  - decide where to place it in main memory
  - *Least Recently Used* replacement scheme

The operating system is a process

The tables controlling the memory are in the memory.

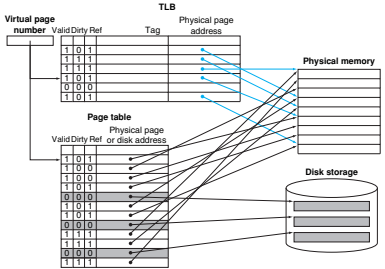
We need to access to the memory to access to the memory!

Virtual memory

Making the translation fast

Definition

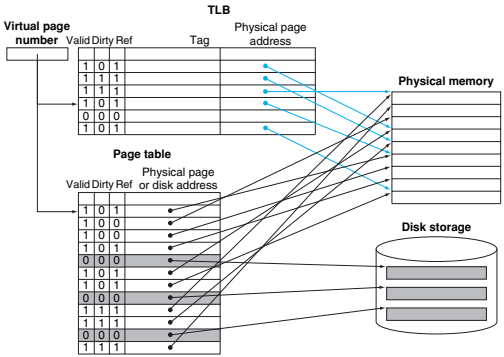
TLB: translation-lookaside buffer. A cache that keeps track of recently used address mappings to try to avoid an access to the page table



The TLB acts as a cache of the page table for the entries that map to physical pages only [11]

Virtual memory

Making the translation fast



The TLB acts as a cache of the page table for the entries that map to physical pages only [11]

TLB

- TLB is a cache, it must have a tag field
- If TLB miss, check the page table
- Typical values:
  - TLB size: 16-512 entries
  - Block size: 1-2 page table entries
  - Miss penalty: 10-100 clock cycles
  - Miss rate: 0.01%-1%

Virtual memory

Putting it all together: Virtual memory, TLBs, and Caches

Interaction

- Virtual memory and cache systems work together
- Under the supervision of the operating system

Best case

Virtual address translated by TLB, sent to cache where data is found, retrieved and sent back to the processor

Worst case

Miss in all three components: TLB, page table, cache

Virtual memory

TLB	Page table	Cache	Possible? If so, under what circumstance?
Hit	Hit	Miss	Possible, although the page table is never really checked if TLB hits.
Miss	Hit	Hit	TLB misses, but entry found in page table; after retry, data is found in cache.
Miss	Hit	Miss	TLB misses, but entry found in page table; after retry, data misses in cache.
Miss	Miss	Miss	TLB misses and is followed by a page fault; after retry, data must miss in cache.
Hit	Miss	Miss	Impossible: cannot have a translation in TLB if page is not present in memory.
Hit	Miss	Hit	Impossible: cannot have a translation in TLB if page is not present in memory.
Miss	Miss	Hit	Impossible: data cannot be allowed in cache if the page is not in memory.

The possible combinations of events in the TLB, virtual memory system and cache [11]

Virtual memory

Implementing protection

Context

Sharing a single main memory by multiple processes

Three basic capabilities:

1. *Supervisor mode* (or *kernel mode*): mode indicating that a running process is an operating system process.
2. Processor state readable (but not writable) by a user process: user/supervisor mode bit + page table pointer + TLB
3. From user mode to supervisor mode (and vice versa):
   - *System call*: special instruction that transfers control from user mode to a dedicated location in supervisor code space, invoking the exception mechanism in the process
   - *Supervisor exception return*: resets to user mode

Virtual memory

Implementing protection

Context

Sharing a single main memory by multiple users

Preventing reading and writing by another (user) process

- Each process has its own virtual space
- The operating system keeps the page tables
- The user process cannot change its own page table
- All page tables placed in a protected address space

Virtual memory

Context switch

Definition

Context switch: changing of the internal state of the processor to allow a different process to use the processor that includes saving the state needed to return to the currently executing process

Overhead

- clear TLB entries
- Inefficient when high process switch rate

Process identifier

- Concatenated to the tag
- TLB hit when
  - Page number + process identifier match

Virtual memory

Memory hierarchy design challenges

Design change	Effect on miss rate	Possible negative performance effect
Increases cache size	Decreases capacity misses	May increase access time
Increases associativity	Decreases miss rate due to conflict misses	May increase access time
Increases block size	Decreases miss rate for a wide range of block sizes due to spatial locality	Increases miss penalty. Very large block could increase miss rate

Source: [11]

Virtual memory

Summary

Virtual memory

- Manage caching between the main memory and secondary memory
- Virtual address (beyond physical address)
- Share main memory between several processes, users with protections

High cost of page fault

Miss rate reduced by

- Large page: spatial locality $\searrow$ miss rate
- Fully associative mapping between virtual and physical addresses
- LRU replacement technique (OS)
- Write-back scheme
- TLB: cache for translations

The future

Still ever increasing technology achievements

Three technologies as the leading contenders [7] (2014):

- STT-RAM (spin-transfer torque RAM) [Mos05]
- PCM (phase-change memory) [Rao08,Lee09]
- Memristor [Stru08]

Emerging nonvolatile memory

spin torque transfer random access memory (STT-RAM), phase change memory (PCM), resistive random access memory (RRAM), racetrack memory (RM), ferromagnetique RAM (FeRAM), etc.

Guangyu Sun, Jishen Zhao, Matt Poremba, Cong Xu, Yuan Xie, *Memory that never forgets: emerging nonvolatile memory and the implication for architecture design*, National Science Review, July 2018

The future

Still ever increasing technology achievements

Embedded COMPUTING DESIGN

Arm Debuts eMRAM IoT test chip with Samsung, Cadence

BRANDON LEWIS MAY 15, 2019

SAMSUNG FOUNDRY FORUM. Arm, Samsung Foundry, Cadence, and Sondrel have collaborated on the Musca-S1, a 28 nm fully-depleted silicon-on-insulator (FD-SOI) embedded MagnetoResistive RAM (eMRAM) test chip based on Arm Cortex-M33 IP. The Musca-S1 test chip and an accompanying development board enable IoT SoC designers to evaluate eMRAM technology, which can easily scale below 40 nm to support a broad range of memory and power requirements.

Source: arm.com

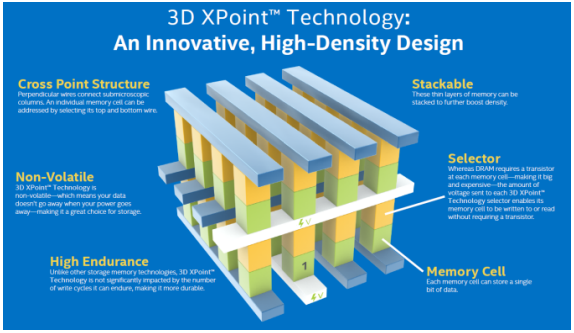
The future

3D XPoint

4th August 2015

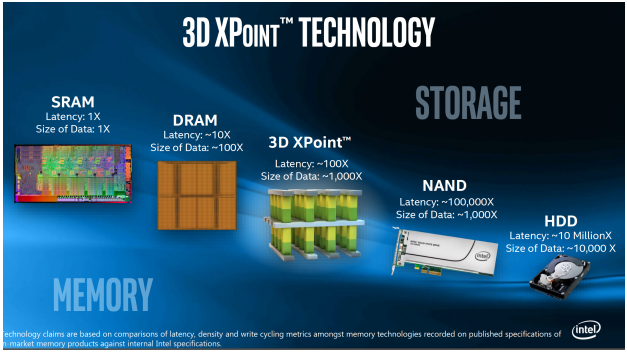
New memory technology is 1,000 times faster

Intel and Micron have unveiled "3D XPoint" – a new memory technology that is 1,000 times faster than NAND and 10 times denser than conventional DRAM.



The future

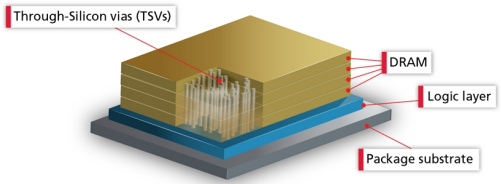
3D XPoint



Commercial product: Optane SSD PC P4800X

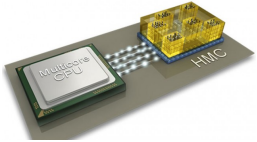
The future

Hybrid Memory Cube



HMC Memory Chip Architecture

https://community.cadence.com/cadence_blogs_8/b/ip/posts/what-s-new-with-hybrid-memory-cube-hmc



The future

Still ever increasing technology achievements

Still...

- more than 80% of the chip area is dedicated to caches, memories, memory controllers, interconnects and so on, whose sole purpose is to buffer data or control the buffering of data [1]

$\Rightarrow$ workarounds which are making systems ever more complex

- more than 62% of the entire measured system energy is spent on moving data between memory and the computation units [1]

Enabling the continued performance scaling of smaller systems requires significant research breakthroughs in three key areas [6]

1. power efficiency
2. programmability
3. execution granularity

Down with Hierarchy!

The future

Stop or reduce moving data

Process the data where it is: in the memory!

AI workloads

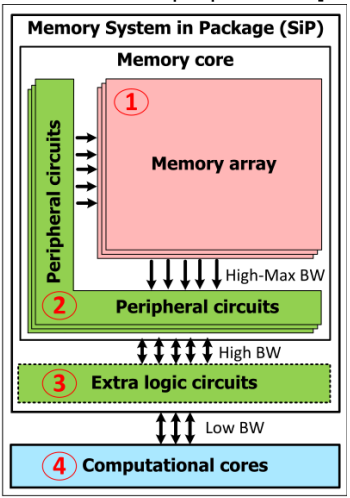
Low arithmetic intensity, lots of memory accesses

Sort this out!

Computing-In-Memory, Processing In Memory, In-memory computing,
Logic In Memory, Near-Memory Computing, Intelligent Memory,
Smart memories, Near-memory processing, Active memory, Memory-driven computing

Classification

Classification proposed in [10]



1. CIM-Array (CIM-A): the computing result is produced within the array
2. CIM-Periphery (CIM-P): the computing result is produced within the peripheral circuitry
3. Computation-Outside-Memory Near (COM-N): inside the memory SiP (System in Package)
4. Computation-Outside-Memory Far (COM-F): traditional computational cores

[10] H. A. D. Nguyen, J. Yu, M. A. Lebdeh, M. Taouil, S. Hamdioui, and F. Catthoor. *A classification of memory-centric computing.* J. Emerg. Technol. Comput. Syst., 16(2), jan 2020.

Processing close to memory

Back to the future!

Hitting the Memory Wall: Implications of the Obvious

Wm. A. Wulf
Sally A. McKee

Department of Computer Science
University of Virginia
{wulf | mckee}@virginia.edu

December 1994

Processing in Memory: The Terasys Massively Parallel PIM Array

Maya Gokhale
David Sarnoff Research Center*

Bill Holmes and Ken Iobst
Supercomputing Research Center

**The work reported here was done while the author was at the Supercomputing Research Center, Bowie, Maryland.*

SIMD processor arrays provide superior performance on fine-grained massively parallel problems in which all parallel threads do the same operations most of the time. However, this fine-grained synchrony limits the application space of SIMD (single instruction, multiple data) machines. If there are many alternative data-dependent actions among the parallel threads, the total execution time is the *sum* of the alternatives rather than the maximum single-thread execution time. Additionally, if the application is not inherently load-balanced, performance can degrade seriously: Most of the processors

Processing close to memory

Where to compute then?

In DRAM

- Processing in memory: inside DRAM (UpMem)
- In-memory computing primarily relies on keeping data in a server's RAM as a means of processing at faster speeds

Source: https://www.upmem.com/

Processing close to memory

Where to compute then?

In SRAM

- X-SRAM: Enabling In-Memory Boolean Computations in CMOS Static Random Access Memories [4] (2018)
  - 75% of memory accesses can be saved
- XNOR-SRAM: In-Memory Computing SRAM Macro for Binary/Ternary Deep Neural Networks [9] (2018)
  - 33X better energy and 300X better energy-delay product

In cache

- Compute cache [3] (2017)
  - performance by 1.9× and reduce energy by 2.4×
  - 54× throughput, 9× dynamic energy savings

Memory-Driven Computing

THE machine

HP bets it all on The Machine, a new computer architecture based on memristors and silicon photonics

By Sebastian Anthony on June 11, 2014 at 11:30 am | 39 Comments

What happened to the HP machine?

Anyone remember the HP announcement about 'the machine'? Billy MacInnes does and he wonders just what has happened to the grand project

HP Enterprise unveils The Machine, a single-memory computer capable of addressing 160 terabytes

DEAN TAKAHASHI @DEANTAK MAY 16, 2017 6:01 AM

WHAT'S NEW

HPE Persistent Memory, available in 128, 256, and 512 GB kits, features Intel® Optane™ DC Persistent Memory to approach the speed of traditional DRAM with the persistence of storage, ensuring high capacity, high performance, and ongoing data safety — even in the event of an interruption in power due to an unexpected power loss, system crash, or normal system shutdown.

The future

Active Research

Displaying results **1-25** of **119** for **(("Document Title":in-memory) AND "Document Title":processing)** ×
Filters Applied: Conferences × Journals & Magazines ×

Displaying results **1-25** of **136** for **(("Document Title":in-memory) AND "Document Title":computing)** :
Filters Applied: Conferences × Journals & Magazines ×

Year	In-memory AND processing	In-memory AND computing
2021	49	202
2020	43	112
2019	48	76
2018	30	51
2017	31	32
2016	17	18
2015	9	16
2014	3	4
2013	1	4
2012	0	0
2011	0	0
1995-2010	18	3

Conclusion

Memory system

- Central component of any digital device
- Keep the pace with faster processors
  - Principle of locality
  - Memory hierarchy

Von Neumann architecture

Computer architecture heavily rely on a 70 years old scheme

Many additional features to get higher performance

The future

- Still rely on technology improvements?
- How to stop useless and (energy) wasteful memory accesses?
- New memory organisations and computing paradigms

THE MEMORY REMAINS !

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